

Please delete the paragraph starting on page 9, line 25, and ending on page 10, line 4.

On page 123, delete the section of the specification entitled ABSTRACT OF THE DISCLOSURE, and replace such deleted section with the following replacement section:

"ABSTRACT OF THE DISCLOSURE

B²
A semiconductor device comprises a semiconductor substrate of a first conductivity type, at least one first well of a second conductivity type formed in the semiconductor substrate, and at least one second well of the first conductivity type formed in at least one first well. The semiconductor device is composed of semiconductor circuits each formed in at least one first well and at least one second well."

IN THE CLAIMS:

Please cancel claims 5-19 without prejudice or disclaimer.

Please replace the text of claim 21 with the following text:

B³
21. (Amended) A semiconductor device comprising:
a semiconductor substrate of a first conductivity type;
at least one first well of a second conductivity type formed in the semiconductor substrate;
at least one second well of the first conductivity type formed in at least one first well; and
at least one third well of the second conductivity type formed in at least one first well,
wherein
the semiconductor device is composed of semiconductor circuits each formed in at least one first well, at least one second well and at least one third well.